



IN THE
UNITED STATES PATENT AND TRADEMARK OFFICE

INVENTOR: Kirk D. Prall et al.

SERIAL NO.: 09/503,638

GROUP ART UNIT: 2814

FILED: February 14, 2000

EXAMINER: G. Peralta

TITLE: Random Access Memory

THE COMMISSIONER OF PATENTS AND TRADEMARKS
WASHINGTON, D.C. 20231

AMENDMENT ACCOMPANYING REQUEST FOR CONTINUED EXAMINATION

Amendments to the Claims

23.(currently amended) A semiconductor memory device, comprising:
a silicon structure having a first conductivity type;
a gate electrode over the silicon structure;
a capacitor contact region in the silicon structure adjacent to one side of the gate electrode;
a bit line contact region in the silicon structure adjacent to the other side of the gate electrode;
a first dopant implant in the capacitor and bit line contact regions, the first dopant having a second conductivity type opposite the first conductivity type and the first dopant implant physically contacting the capacitor contact region; and
a second dopant implant in only the capacitor contact region.

24.(original) A device according to Claim 23, wherein the second dopant implant is deeper than the first dopant implant.